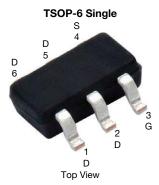


# Automotive P-Channel 20 V (D-S) 175 °C MOSFET



#### Marking Code: 8Z

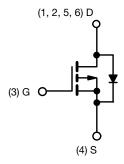
PRODUCT SUMMARY				
V <sub>DS</sub> (V)	-20			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 \text{ V}$	0.060			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -2.5 \text{ V}$	0.100			
I <sub>D</sub> (A)	-7.4			
Configuration	Single			

#### **FEATURES**

- TrenchFET® power MOSFET
- AEC-Q101 qualified c
- 100 % R<sub>q</sub> and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



ROHS COMPLIANT HALOGEN FREE



P-Channel MOSFET

ORDERING INFORMATION	
Package	TSOP-6
Lead (Pb)-free and halogen-free	SQ3425EV (for detailed order number please see <a href="https://www.vishay.com/doc?79771">www.vishay.com/doc?79771</a> )

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V <sub>DS</sub>	-20		
Gate-source voltage		V <sub>GS</sub> ± 12		- V	
Continuous drain current	T <sub>C</sub> = 25 °C	I-	-7.4		
	T <sub>C</sub> = 125 °C	l <sub>D</sub>	-4.3		
Continuous source current (diode conduction	I <sub>S</sub>	-4.5	Α		
Pulsed drain current <sup>a</sup>		I <sub>DM</sub>	-29		
Single pulse avalanche current	L = 0.1 mH	I <sub>AS</sub>	-11		
Single pulse avalanche energy	L = 0.1 IIII	E <sub>AS</sub>	6	mJ	
Maximum power dissipation <sup>a</sup>	T <sub>C</sub> = 25 °C	0	5	W	
	T <sub>C</sub> = 125 °C	P <sub>D</sub>	1.67	] vv	
Operating junction and storage temperature	range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-ambient	PCB mount b	$R_{thJA}$	110	°C/W	
Junction-to-foot (drain)		$R_{thJF}$	30	C/VV	

#### Notes

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %
- b. When mounted on 1" square PCB (FR4 material)
- c. Parametric verification ongoing



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PARAMETER	SYMBOL	TES	MIN.	TYP.	MAX.	UNIT	
Static	1	-					
Drain-source breakdown voltage	V <sub>DS</sub>	$V_{GS} = 0$ , $I_D = -250 \mu A$		-20	-	-	V
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$		-1	-1.4	V
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$		-	± 100	nA
		$V_{GS} = 0 V$	V <sub>DS</sub> = -20 V	-	-	-1	
Zero gate voltage drain current	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = -20 V, T <sub>J</sub> = 125 °C	1	-	-50	μΑ
		$V_{GS} = 0 V$	V <sub>DS</sub> = -20 V, T <sub>J</sub> = 175 °C	=	-	-150	]
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = -4.5 V	V <sub>DS</sub> ≤ -5 V	-15	-	-	Α
		V <sub>GS</sub> = -4.5 V	I <sub>D</sub> = -4.7 A	=	0.049	0.060	
Drain acuras an atata registance 3	В	V <sub>GS</sub> = -4.5 V	I <sub>D</sub> = -4.7 A, T <sub>J</sub> = 125 °C	-	0.065	-	
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = -4.5 V	I <sub>D</sub> = -4.7 A, T <sub>J</sub> = 175 °C	=	0.074	-	Ω
		V <sub>GS</sub> = -2.5 V	I <sub>D</sub> = -1 A	=	0.089	0.100	
Forward transconductance <sup>a</sup>	9fs	V <sub>DS</sub> =	$V_{DS} = -10 \text{ V}, I_D = -4.7 \text{ A}$		9	_	S
Dynamic <sup>b</sup>		•					
Input capacitance	C <sub>iss</sub>			1	560	840	
Output capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = -10 V, f = 1 MHz	-	178	267	pF
Reverse transfer capacitance	C <sub>rss</sub>			=	126	190	
Total gate charge <sup>c</sup>	Qg			=	6.9	10.3	
Gate-source charge <sup>c</sup>	$Q_{gs}$	$V_{GS} = -4.5 \text{ V}$	$V_{DS} = -10 \text{ V}, I_D = -4.7 \text{ A}$	-	1.2	-	nC
Gate-drain charge <sup>c</sup>	Q <sub>gd</sub>			=	2.6	-	
Gate resistance	R <sub>g</sub>		f = 1 MHz		6.1	9.1	Ω
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>			-	11	15	
Rise time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = -10 \text{ V}, \text{ R}_L = 10 \Omega$ $I_D \cong -1 \text{ A}, \text{ V}_{GEN} = -4.5 \text{ V}, \text{ R}_g = 6 \Omega$		-	26	35	ns ns
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>			-	41	55	
Fall time <sup>c</sup>	t <sub>f</sub>			-	28	38	
Source-Drain Diode Ratings and Char	racteristics <sup>b</sup>						
Pulsed current <sup>a</sup>	I <sub>SM</sub>			-	-	-21	Α
Forward voltage	V <sub>SD</sub>	I <sub>F</sub> =	I <sub>F</sub> = -1.7 A, V <sub>GS</sub> = 0 V		-0.8	-1.2	V
	•	•					

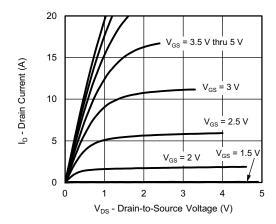
#### Notes

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

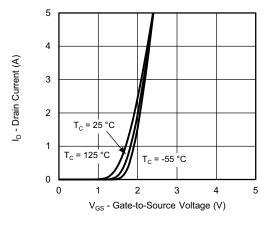
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



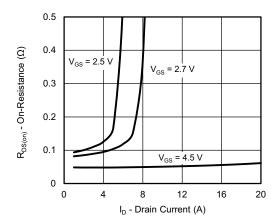
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



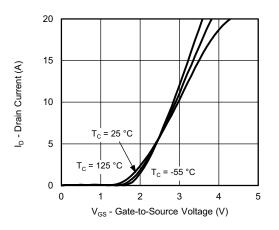
#### **Output Characteristics**



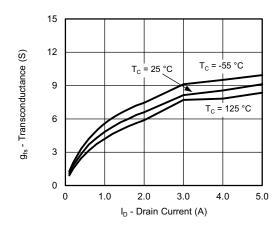
### Transfer Characteristics



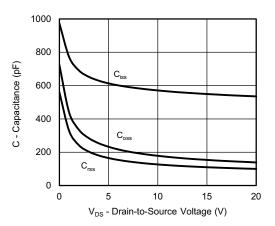
On-Resistance vs. Drain Current



#### **Transfer Characteristics**



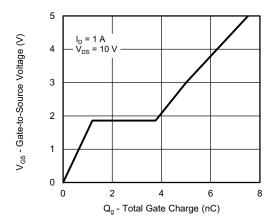
#### Transconductance



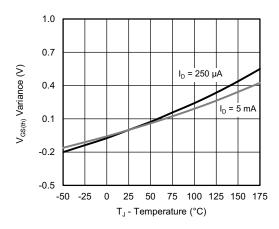
Capacitance



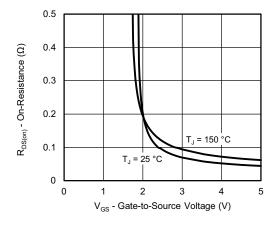
### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



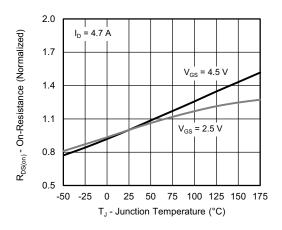
#### **Gate Charge**



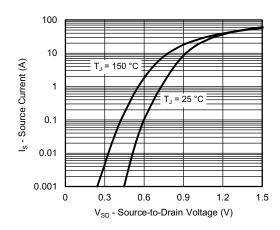
#### **Threshold Voltage**



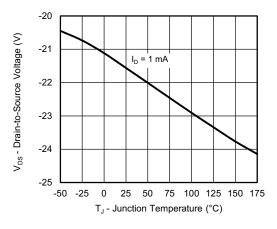
On-Resistance vs. Gate-to-Source Voltage



#### On-Resistance vs. Junction Temperature



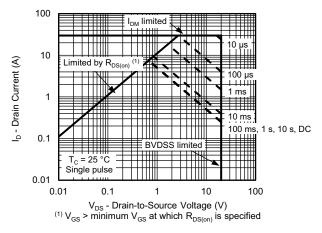
#### **Source Drain Diode Forward Voltage**



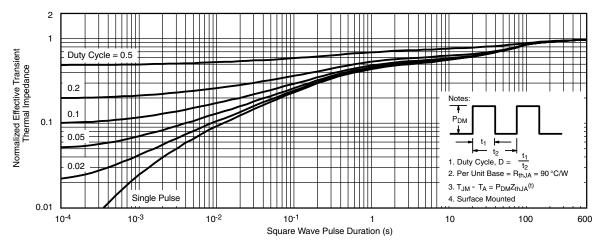
**Drain Source Breakdown vs. Junction Temperature** 



## **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)



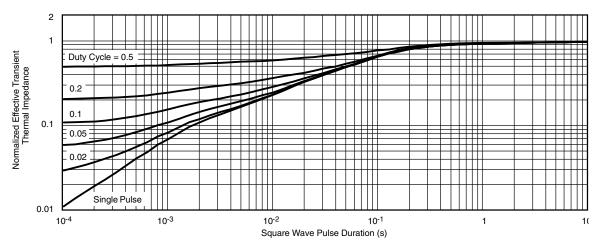
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



## THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

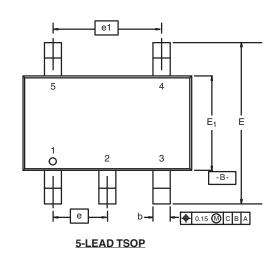
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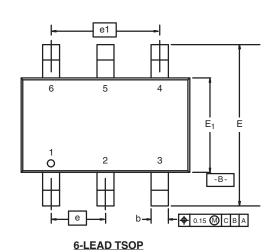


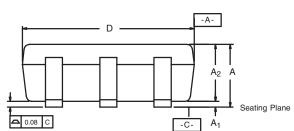


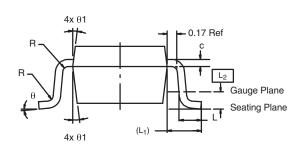
TSOP: 5/6-LEAD

**JEDEC Part Number: MO-193C** 









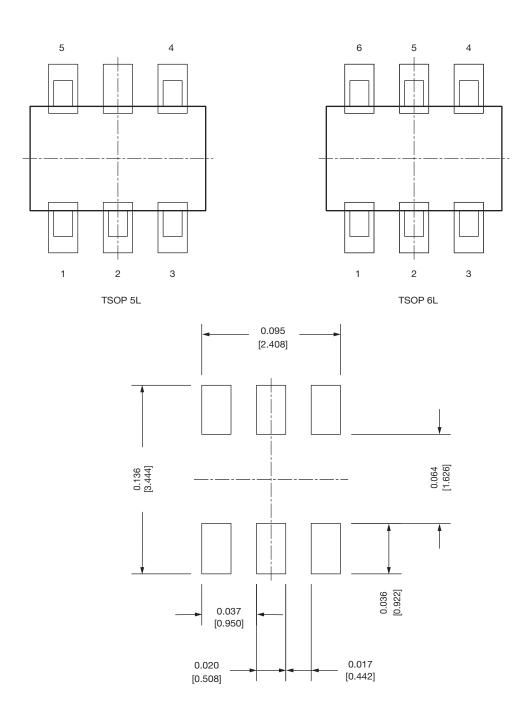
	MILLIMETERS			INCHES		
Dim	Min	Nom	Max	Min	Nom	Max
Α	0.91	-	1.10	0.036	-	0.043
A <sub>1</sub>	0.01	-	0.10	0.0004	-	0.004
A <sub>2</sub>	0.90	-	1.00	0.035	0.038	0.039
b	0.30	0.32	0.45	0.012	0.013	0.018
С	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
E	2.70	2.85	2.98	0.106	0.112	0.117
E <sub>1</sub>	1.55	1.65	1.70	0.061	0.065	0.067
е		0.95 BSC		0.0374 BSC		
e <sub>1</sub>	1.80	1.90	2.00	0.071	0.075	0.079
L	0.32	-	0.50	0.012	-	0.020
L <sub>1</sub>	0.60 Ref			0.024 Ref		
L <sub>2</sub>		0.25 BSC		0.010 BSC		
R	0.10	-	-	0.004	-	-
θ	0°	4°	8°	0°	4°	8°
$\theta_1$		7° Nom 7° Nom				
ECN: C-06593-Rev. I, 18-Dec-06 DWG: 5540						

Document Number: 71200

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## Recommended Land Pattern For TSOP-5L / TSOP-6L



### Note

• All dimensions are in inches (millimeter)

ECN: C22-0860-Rev. B, 24-Oct-2022 DWG: 3010



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